

What is claimed is:

1. A free-standing etching solution for the wet chemical pyramidal texture etching of silicon surfaces comprising: water, an alkaline reagent, isopropanol and an aqueous alkaline ethylene glycol solution.

5 2. The free-standing etching solution as in claim 1, wherein the etching solution further comprises silicate.

3. The free-standing etching solution as in claim 1, wherein the etching solution contains 0.5 to 5 vol% isopropanol.

10 4. The free-standing etching solution as in claim 1, wherein the proportion of isopropanol present in the etching solution is greater than the proportion of ethylene glycol.

5. The free-standing etching solution as in claim 4, wherein the ratio of isopropanol the ethylene glycol is at maximum 1:1.

6. The free-standing etching solution as in claim 1, wherein the aqueous alkaline ethylene glycol solution is reacted with oxygen.

15 7. A free-standing etching solution for the wet chemical pyramidal texture etching of silicon surfaces comprising: water, sodium or potassium hydroxide, isopropanol and an aqueous alkaline ethylene glycol solution.

8. The free-standing etching solution as in claim 7, further comprising silicate.

20 9. The free-standing etching solution as in claim 7, wherein the etching solution contains 0.5 to 5 vol.% isopropanol.

10. The free-standing etching solution as in claim 7, wherein the proportion of isopropanol present in the etching solution is greater than the proportion of ethylene glycol.

11. The free-standing etching solution as in claim 10, wherein the ratio of isopropanol to ethylene glycol is at maximum 1:1.

5 12. The free-standing etching solution as in claim 7, wherein the aqueous alkaline ethylene glycol solution is reacted with oxygen.